

1. Scope :

This specification applies to P/N silicon TVS diode chips,
Device NO. SD-113B6

2. Structure :

- 2-1. Planar type : P/N Diode.
- 2-2. Electrodes :
Top side : Aluminum alloy.
Back side : Gold layer.

3. Size :

- 3-1. Chip size : 15.4 mils x 10.6 mils (0.390 mm x 0.270 mm).
- 3-2. Chip thickness : 5.9 ± 1.0 mils (0.150 ± 0.0254 mm)
- 3-3. Bonding pad : 10.6 mils x 5.9 mils (0.270 mm x 0.150 mm).
- 3-4. Pattern drawing : Refer to the attached drawing.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Current	I_R	$V_R=29V$ $E_e=0mW/cm^2$			600	nA
Reverse Breakdown Voltage	$V_{(BR)}$	$I_R=5mA$ $E_e=0mW/cm^2$	34		38	V
Forward Voltage	V_f	$I_F=10mA$ $E_e=0mW/cm^2$			1.2	V

